

SEBT8550

EPITAXIAL PLANAR PNP TRANSISTOR

Features

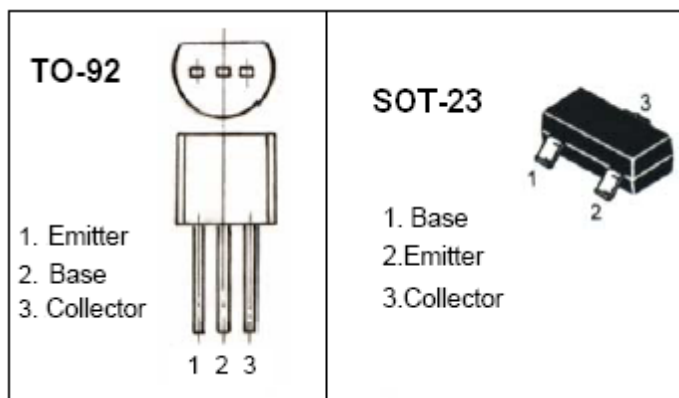
- Complementary to SEBT8550

Applications

- HIGH CURRENT APPLICATION

Construction

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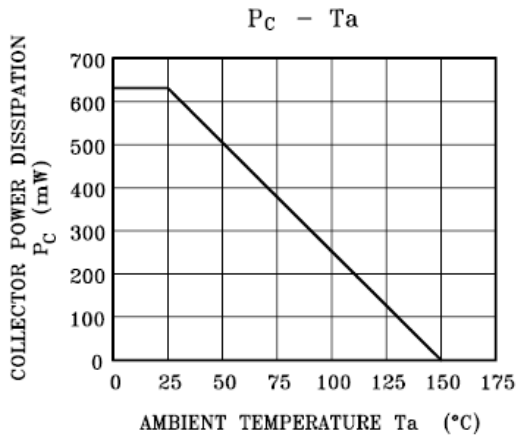
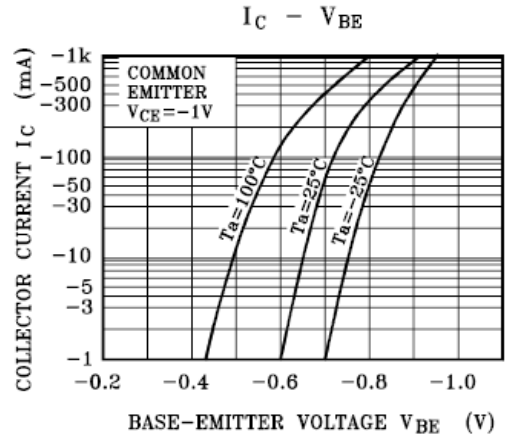
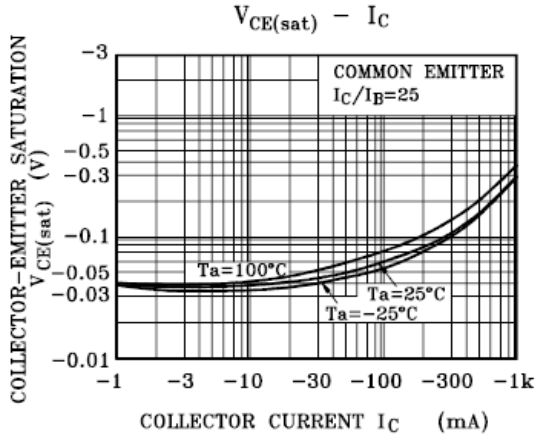
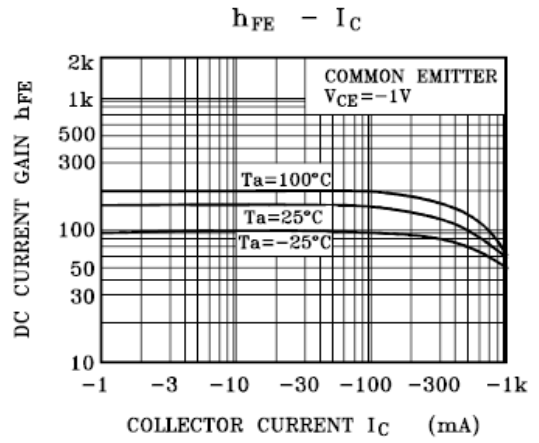
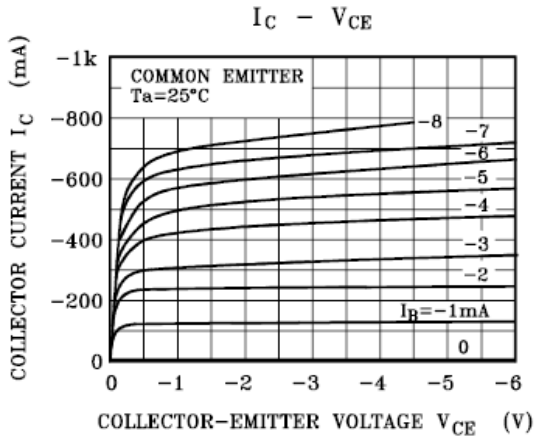
Maximum Ratings (Ta=25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|-----------------------------|-----------|------------|------|
| Collector-Base Voltage | V_{CBO} | -35 | V |
| Collector-Emitter Voltage | V_{CEO} | -30 | V |
| Emitter-Base Voltage | V_{EBO} | -5 | V |
| Collector Current | I_C | 1500 | mA |
| Emitter Current | I_E | 800 | mA |
| Collector Power Dissipation | P_C | 625 | mW |
| Junction temperature | T_j | 150 | °C |
| Storage temperature Range | T_{stg} | -55 ~ +150 | °C |

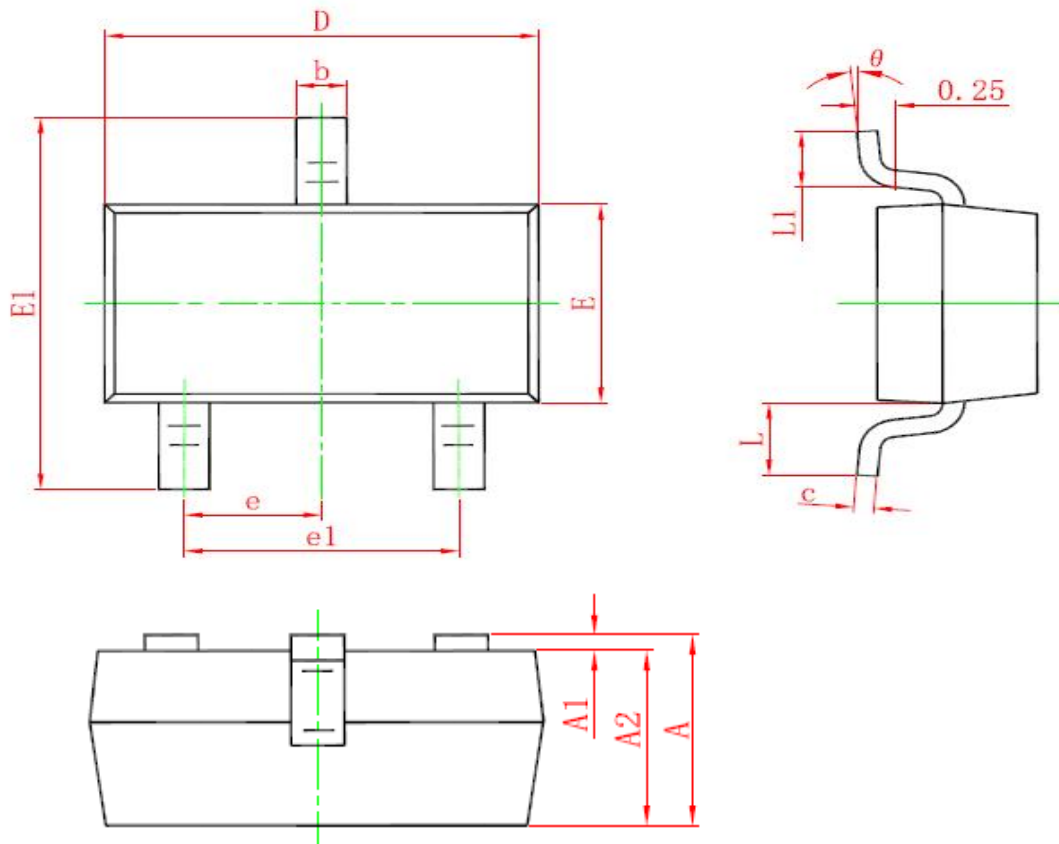
Electrical characteristics (Ta=25°C)

| Characteristic | Symbol | Test Condition | MIN | TYP. | MAX | UNIT |
|--------------------------------------|-----------------------|--------------------------|-----|------|-----|------|
| Collector Cut-off Current | I_{CBO} | $V_{CB}=-15v$ | - | - | -50 | nA |
| Collector-Base Breakdown Voltage | $V_{(BR) CBO}$ | $I_C=-0.5mA$ | -35 | - | - | V |
| Collector-Emitter Breakdown Voltage | $V_{(BR) CEO}$ | $I_C=-1mA$ | -30 | - | - | V |
| DC Current Gain | $h_{FE(1)}$ (Note) | $V_{CE}=-1v, I_C=-50mA$ | 100 | - | 300 | |
| | $h_{FE(2)}$ | $V_{CE}=-1v, I_C=-350mA$ | 60 | - | - | |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=-500mA, I_B=-50mA$ | - | - | 0.5 | V |
| Base-Emitter Voltage | V_{BE} | $V_{CE}=-1v, I_C=-500mA$ | - | - | 1.2 | V |
| Transition Frequency | f_r | $V_{CE}=-1v, I_C=-10mA$ | - | 120 | - | MHz |
| Collector Output Capacitance | C_{ob} | $V_{CB}=-10V, f=1MHz,$ | - | 19 | - | pF |

Note: $h_{FE(1)}$ Classification C : 100~200, D : 150~300

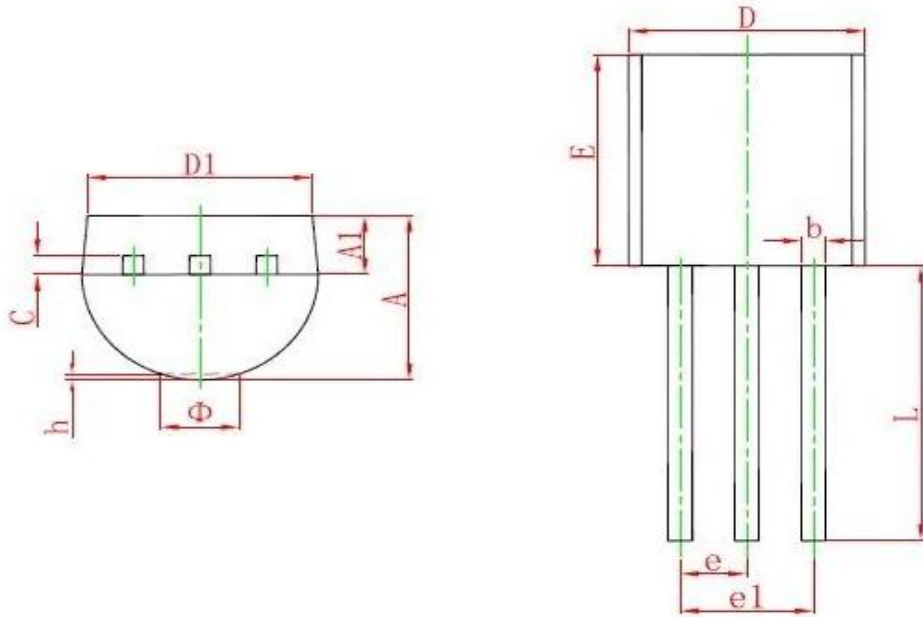


SOT-23 PACKAGE OUTLINE DIMENSIONS



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 TYP. | | 0.037 TYP. | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 REF. | | 0.022 REF. | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |

TO-92 PACKAGE OUTLINE DIMENSIONS



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|--------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 3.300 | 3.700 | 0.130 | 0.146 |
| A1 | 1.100 | 1.400 | 0.043 | 0.055 |
| b | 0.380 | 0.550 | 0.015 | 0.022 |
| c | 0.360 | 0.510 | 0.014 | 0.020 |
| D | 4.400 | 4.700 | 0.173 | 0.185 |
| D1 | 3.430 | | 0.135 | |
| E | 4.300 | 4.700 | 0.169 | 0.185 |
| e | 1.270 TYP | | 0.050 TYP | |
| e1 | 2.440 | 2.640 | 0.096 | 0.104 |
| L | 14.100 | 14.500 | 0.555 | 0.571 |
| Φ | | 1.600 | | 0.063 |
| h | 0.000 | 0.380 | 0.000 | 0.015 |

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